

**Amendments to the Claims:**

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

WHAT IS CLAIMED IS:

1. (Canceled)
2. (Canceled)
3. (Canceled)
4. (Canceled)
5. (Canceled)
6. (Canceled)
7. (Canceled)
8. (Canceled)
9. (Canceled)
10. (Canceled)
11. (Canceled)
12. (Canceled)
13. (Canceled)
14. (Canceled)
15. (Canceled)
16. (Canceled)

17. (Canceled)

18. (Canceled)

19. (Canceled)

20. (Canceled)

21. (Canceled)

22. (Canceled)

23. (Canceled)

24. (Canceled)

25. (Canceled)

26. (Canceled)

27. (New) A method for forming a dielectric film comprising:

forming a silicon film directly or indirectly on at least a part of a glass substrate, a plastic substrate or a silicon monocrystalline wafer;

forming a first silicon oxide film by subjecting said silicon film to an oxidation treatment in a plasma comprised of a gaseous mixture of krypton and oxygen; and

forming a second silicon oxide film on said first silicon oxide film by a plasma enhanced chemical vapor deposition method.

28. (New) A method for forming a dielectric film comprising:

forming a silicon film directly or indirectly on at least a part of a glass substrate, a plastic substrate or a silicon monocrystalline wafer;

forming a silicon nitride film by subjecting said silicon film to a nitriding treatment in a plasma comprised of a gaseous mixture of argon and nitrogen; and

forming a silicon oxide film on said silicon nitride film by a plasma enhanced chemical vapor deposition method.

29. (New) A method for producing a thin film transistor comprising:

forming a polycrystalline silicon film directly or indirectly on at least a part of a glass substrate, a plastic substrate or a silicon monocrystalline wafer;

forming a gate insulating film on said polycrystalline silicon film;

forming a gate electrode on said gate insulating film; and

forming a source region and a drain region on a part of said polycrystalline silicon film,

wherein said gate insulating film is formed by creating a first silicon oxide film by subjecting said polycrystalline silicon film to an oxidation treatment in a plasma comprised of a gaseous mixture of krypton and oxygen, and forming a second silicon oxide film on said first silicon oxide film by a plasma enhanced chemical vapor deposition method.

30. A method according to any one of claims 27-29, wherein an underlaying insulating film is formed on said glass substrate, said plastic substrate or said Si monocrystalline wafer.

31. (New) A method according to any one of claims 27-29, wherein said silicon film is a crystallized silicon film.

32. (New) A method according to any one of claims 29-29, wherein the silicon oxide film formed by the plasma enhanced chemical vapor deposition method is formed with a gaseous mixture of TEOS and oxygen by a plasma enhanced chemical vapor deposition method in which a VHF band is used as a frequency band.

33. (New) A method according to any one of claims 27-29, wherein said plasma is a surface wave plasma.

34. (New) A method according to claim 27 or 29, wherein said plasma is comprised of a gaseous mixture of krypton and oxygen is such that a partial pressure of said krypton is  $\geq 90\%$ .